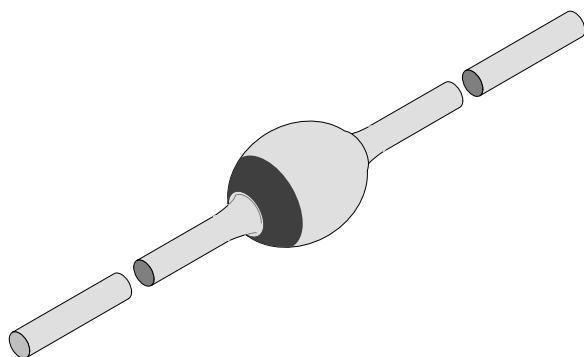


Silicon Z–Diodes and Transient Voltage Suppressors

Features

- Glass passivated junction
- Hermetically sealed package
- Clamping time in picoseconds



94 9539

Applications

Medium power voltage regulators and medium power transient suppression circuits

Absolute Maximum Ratings

 $T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Value	Unit
Power dissipation	I=10mm, $T_L=25^\circ\text{C}$		P _V	3.25	W
	$T_{\text{amb}}=25^\circ\text{C}$		P _V	1.3	W
Repetitive peak reverse power dissipation			P _{ZRM}	10	W
Non repetitive peak surge power dissipation	$t_p=100\mu\text{s}, T_j=25^\circ\text{C}$		P _{ZSM}	600	W
Junction temperature			T _j	175	°C
Storage temperature range			T _{stg}	-65...+175	°C

Maximum Thermal Resistance

 $T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	I=10mm, $T_L=\text{constant}$	R _{thJA}	46	K/W
	on PC board with spacing 25mm	R _{thJA}	100	K/W

Electrical Characteristics

 $T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=0.5\text{A}$		V _F			1.2	V

Type	V _Z			r _{zi}		and		T _{KVZ}	at	I _Z	I _R	at	V _R
BZT03C...	V	V	V	Ω	Ω	%/K	%/K		mA	μA			
	Min.	Typ.	Max.	Typ.	Max.	Min.	Max.					Max.	
6V2	5.8	6.2	6.6	1	2	0	0.07	100	1500	4.7			
6V8	6.4	6.8	7.2	1	2	0	0.07	100	1000	5.1			
7V5	7.0	7.5	7.9	1	2	0	0.07	100	750	5.6			
8V2	7.7	8.2	8.7	1	2	0.03	0.08	100	600	6.2			
9V1	8.5	9.1	9.6	2	4	0.03	0.08	50	20	6.8			
10	9.4	10	10.6	2	4	0.05	0.09	50	10	7.5			
11	10.4	10	11.6	4	7	0.05	0.10	50	4	8.2			
12	11.4	12	12.7	4	7	0.05	0.10	50	3	9.1			
13	12.4	13	14.1	5	10	0.05	0.10	50	2	10			
15	13.8	15	15.6	5	10	0.05	0.10	50	1	11			
16	15.3	16	17.1	6	15	0.06	0.11	25	1	12			
18	16.8	18	19.1	6	15	0.06	0.11	25	1	13			
20	18.8	20	21.2	6	15	0.06	0.11	25	1	15			
22	20.8	22	23.3	6	15	0.06	0.11	25	1	16			
24	22.8	24	25.6	7	15	0.06	0.11	25	1	18			
27	25.1	27	28.9	7	15	0.06	0.11	25	1	20			
30	28	30	32	8	15	0.06	0.11	25	1	22			
33	31	33	35	8	15	0.06	0.11	25	1	24			
36	34	36	38	21	40	0.06	0.11	10	1	27			
39	37	39	41	21	40	0.06	0.11	10	1	30			
43	40	43	46	24	45	0.07	0.12	10	1	33			
47	44	47	50	24	45	0.07	0.12	10	1	36			
51	48	51	54	25	60	0.07	0.12	10	1	39			
56	52	56	60	25	60	0.07	0.12	10	1	43			
62	58	62	66	25	80	0.08	0.13	10	1	47			
68	64	68	72	25	80	0.08	0.13	10	1	51			
75	70	75	79	30	100	0.08	0.13	10	1	56			
82	77	82	87	30	100	0.08	0.13	10	1	62			
91	85	91	96	60	200	0.09	0.13	5	1	68			
100	94	100	106	60	200	0.09	0.13	5	1	75			
110	104	110	116	80	250	0.09	0.13	5	1	82			
120	114	120	127	80	250	0.09	0.13	5	1	91			
130	124	130	141	110	300	0.09	0.13	5	1	100			
150	138	150	156	130	300	0.09	0.13	5	1	110			
160	153	160	171	150	350	0.09	0.13	5	1	120			
180	168	180	191	180	400	0.09	0.13	5	1	130			
200	188	200	212	200	500	0.09	0.13	5	1	150			
220	208	220	233	350	750	0.09	0.13	2	1	160			
240	228	240	256	400	850	0.09	0.13	2	1	180			
270	251	270	289	450	1000	0.09	0.13	2	1	200			

Type	Clamping at		Stand-off at	
	$V_{(CL)R}$ ¹⁾	I_{RSM}	I_R	V_R ²⁾
			μA	V
BZT03C...	V	A		
	Max.		Max.	
6V2	9.3	34.0	3000	5.1
6V8	10.2	31.0	2000	5.6
7V5	11.3	26.5	1500	6.2
8V2	12.3	24.4	1200	6.8
9V1	13.3	22.7	50	7.5
10	14.8	20.3	20	8.2
11	15.7	19.1	5	9.1
12	17.0	17.7	5	10
13	18.9	15.9	5	11
15	20.9	14.4	5	12
16	22.9	13.1	5	13
18	25.6	11.7	5	15
20	28.4	10.6	5	16
22	31.0	9.7	5	18
24	33.8	8.9	5	20
27	38.1	7.9	5	22
30	42.2	7.1	5	24
33	46.2	6.5	5	27
36	50.1	6.0	5	30
39	54.1	5.5	5	33
43	60.7	4.9	5	36
47	65.5	4.6	5	39
51	70.8	4.2	5	43
56	78.6	3.8	5	47
62	86.5	3.5	5	51
68	94.4	3.2	5	56
75	103.5	2.9	5	62
82	114	2.6	5	68
91	126	2.4	5	75
100	139	2.2	5	82
110	152	2.0	5	91
120	167	1.8	5	100
130	185	1.6	5	110
150	204	1.5	5	120
160	224	1.3	5	130
180	249	1.2	5	150
200	276	1.1	5	160
220	305	1.0	5	180
240	336	0.9	5	200
270	380	0.8	5	220

1) 10/1000 exp. falling pulse $t_p = 1000 \mu s$ down to 50%

Characteristics ($T_j = 25^\circ\text{C}$ unless otherwise specified)

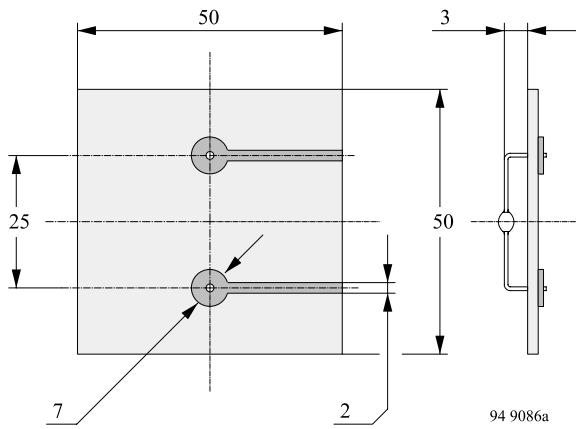


Figure 1. Epoxy glass hard tissue, board thickness 1.5 mm, $R_{thJA} \leq 100 \text{ K/W}$

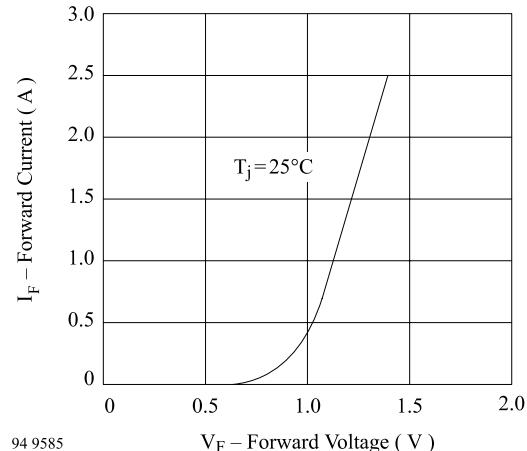


Figure 3. Forward Current vs. Forward Voltage

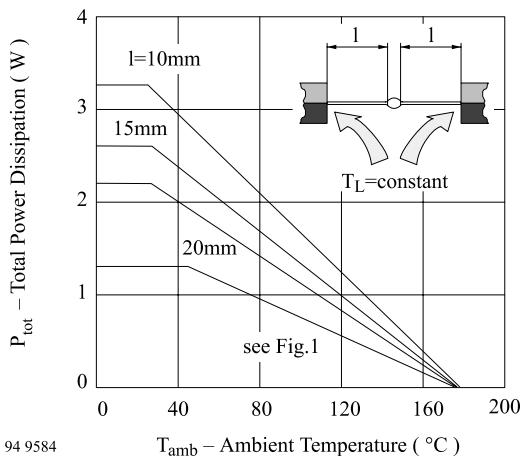


Figure 2. Total Power Dissipation vs.
Ambient Temperature

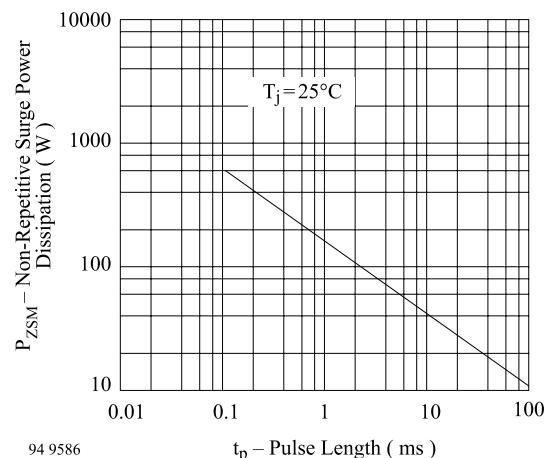
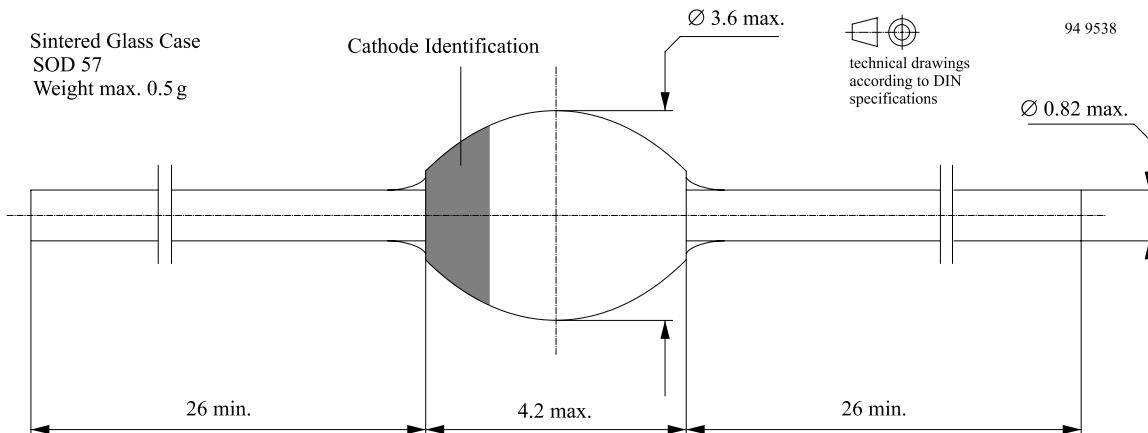


Figure 4. Non Repetitive Surge Power Dissipation vs.
Pulse Length

Dimensions in mm



Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay-Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay-Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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